

Title (en)

BOND STRUCTURES ON MEMS ELEMENT AND ASIC ELEMENT

Title (de)

BOND-STRUKTUREN AUF MEMS-ELEMENT UND ASIC-ELEMENT

Title (fr)

STRUCTURES DE LIAISON SUR L'ÉLÉMENT MEMS ET L'ÉLÉMENT ASIC

Publication

**EP 3774640 A1 20210217 (DE)**

Application

**EP 19711515 A 20190307**

Priority

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- EP 2019055641 W 20190307

Abstract (en)

[origin: WO2019192797A1] The invention relates to a MEMS element (100), comprising: a substrate (10); - a first passivation layer (20) arranged on the substrate (10); - a metal layer (30) arranged on the first passivation layer (20); - a second passivation layer (40) arranged on the metal layer (30) and on the first passivation layer (20); and - a punch element (60), an electrically conductive diffusion-blocking layer (50) being arranged on the punch element (60) and on the second passivation layer (40), a first bonding element (70) being arranged on the punch element (60).

IPC 8 full level

**B81C 1/00** (2006.01)

CPC (source: EP US)

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Citation (search report)

See references of WO 2019192797A1

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**WO 2019192797 A1 20191010**; CN 111936413 A 20201113; DE 102018205156 A1 20191010; EP 3774640 A1 20210217; US 2020399116 A1 20201224

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